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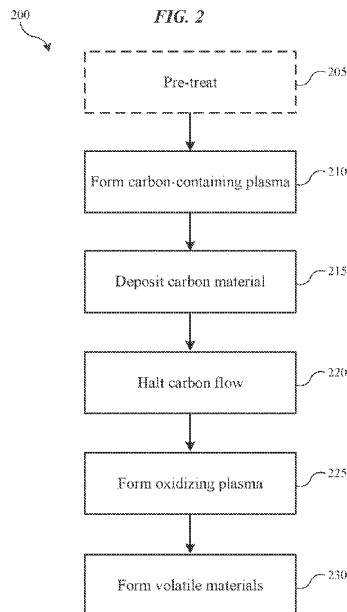
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(54) Title: TREATMENTS FOR CONTROLLING DEPOSITION DEFECTS



(57) Abstract: Exemplary methods of semiconductor processing may include forming a plasma of a carbon-containing precursor in a processing region of a semiconductor processing chamber. The methods may include depositing a carbon-containing material on a substrate housed in the processing region of the semiconductor processing chamber. The methods may include halting a flow of the carbon-containing precursor into the processing region of the semiconductor processing chamber. The methods may include contacting the carbon-containing material with plasma effluents of an oxidizing material. The methods may include forming volatile materials from a surface of the carbon-containing material.

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